

HCS03FT140H5A1S

1400V/600A 3 Phase SiC MOSFET Module

Description

The HCS03FT140H5A1S is a 3 Phase SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips for xEV or motor drives application.



Features

- Blocking Voltage 1400V
- $R_{DS(on)} = 3.2m\Omega$ ($T_j = 25^\circ C$)
- 175°C Maximum Junction Temperature
- Si_3N_4 AMB Substrate
- Direct Cooled Pin Fin Base Plate
- Thermistor Inside
- Press FIT Contact Technology

Application

- xEV Applications
- Motor Drives

Circuit Diagram

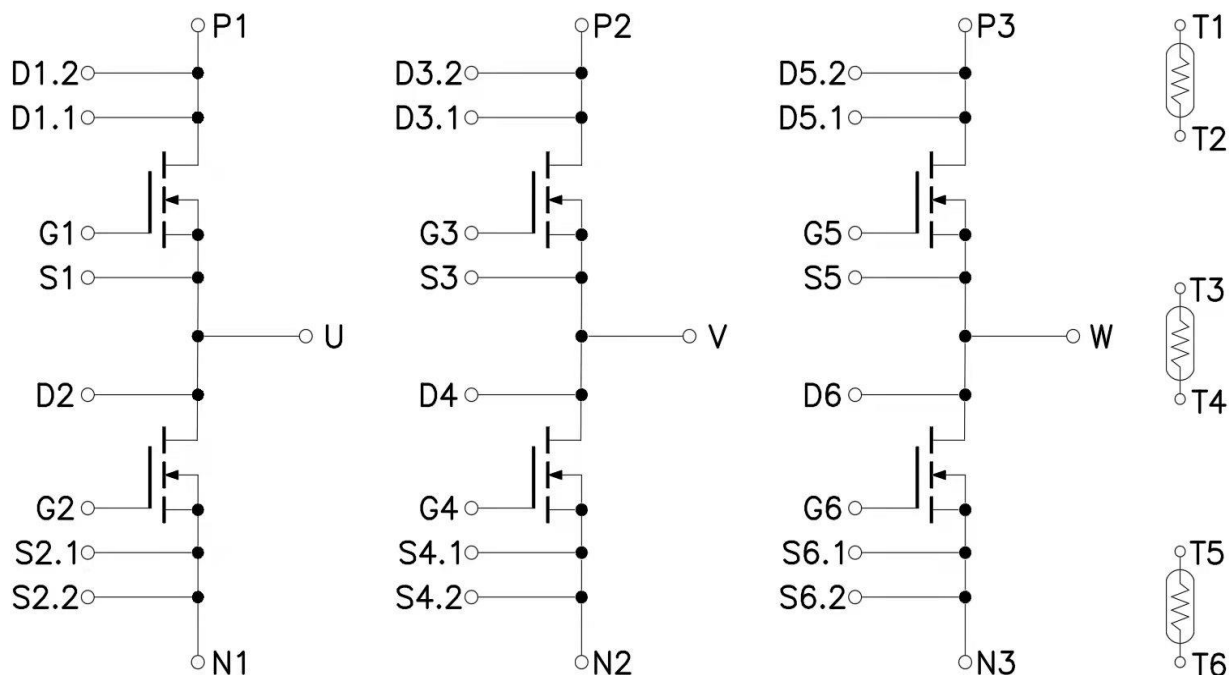


Figure 1. Out Drawing & Circuit Diagram HCS03FT140H5A1S

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Physical Dimensions

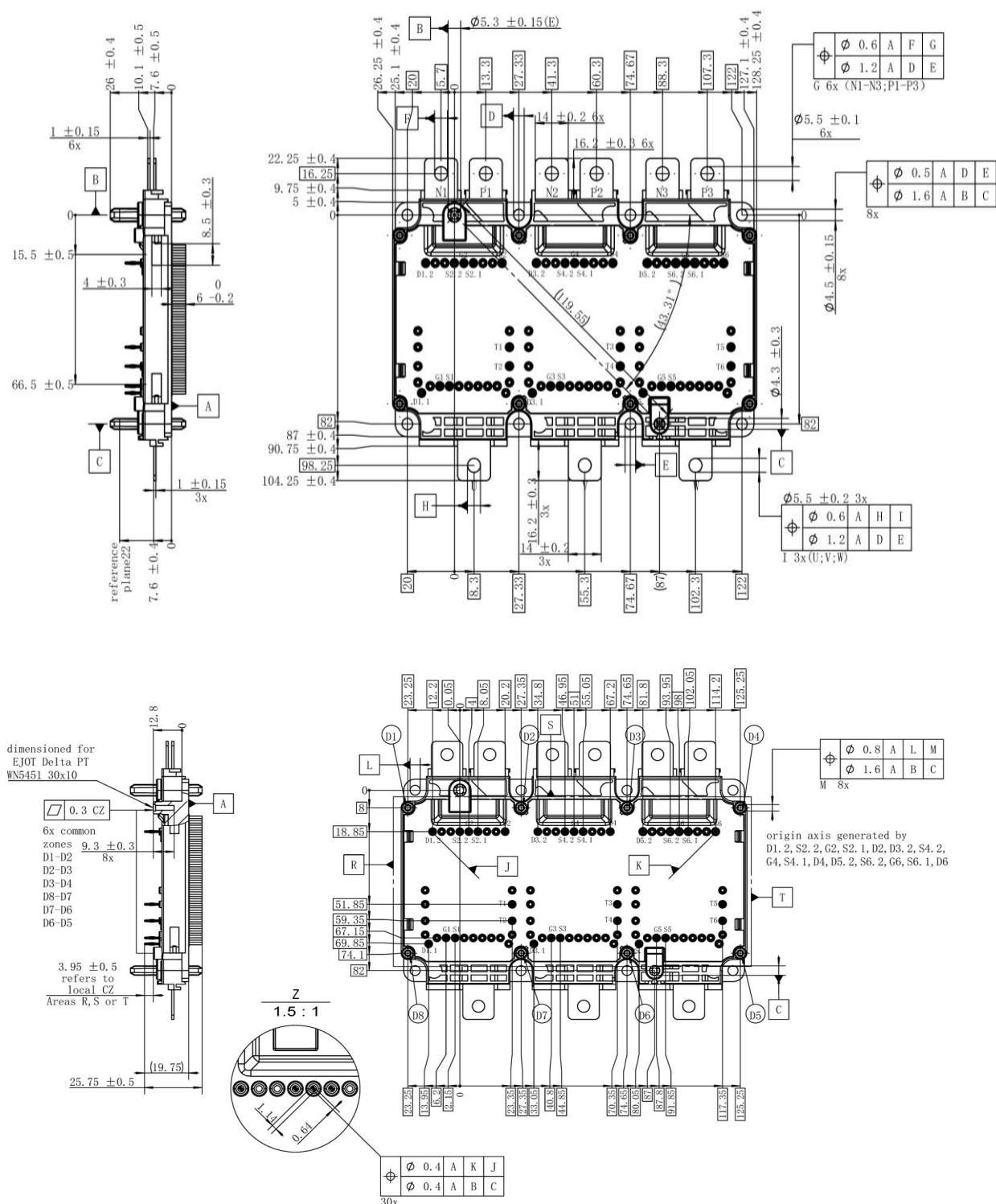


Figure 2. Physical Dimensions

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Maximum Ratings ($T_J=25^{\circ}\text{C}$ Unless Otherwise Specified)

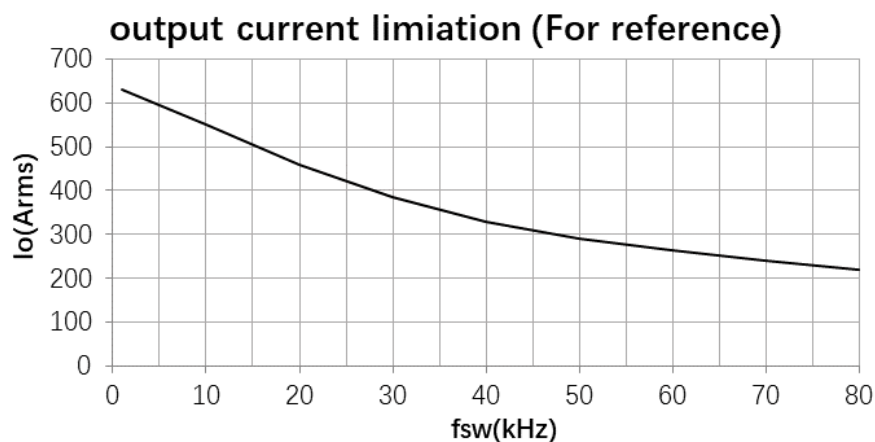
Symbol	Parameter	Conditions	Value	Unit
V_{DSS}	Drain-Source Voltage	G-S Short	1400	V
$V_{\text{DS nom}}$	Continuous Operating DC Voltage	Not include surge voltage	1200	V
V_{GSS}	Gate-Source Voltage	D-S Short, AC frequency • 4Hz, Note1	-10V/+25V	V
I_{DS}	DC Continuous Drain Current	$T_J=25^{\circ}\text{C}$, $V_{\text{GS}}=20\text{V}$	530	A
I_{DS}	DC Continuous Drain Current	$T_J=65^{\circ}\text{C}$, $V_{\text{GS}}=20\text{V}$	460	A
I_{SD}	Source (Body Diode) Current	$T_J=25^{\circ}\text{C}$, with ON signal	530	A
I_{SD}	Source (Body Diode) Current	$T_J=65^{\circ}\text{C}$, with ON signal	460	A
I_{DP}	Drain Pulse Current, Peak	Less than 1ms, Note2	1200	A
P_{D}	Maximum Power Dissipation	$T_J=25^{\circ}\text{C}$	1785	W
T_J	Junction temperature	-	-40 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 to 125	$^{\circ}\text{C}$

Note1: Recommended Operating Value: +20V/-5V, +20V/-4V, +18V/-4V, +15V/-4V

Note2: Pulse width limited by maximum junction temperature

Typical Current Output Ability

Condition: SPWM control, $V_{\text{DD}}=800\text{V}$, $R_{\text{g(ON)}}=R_{\text{g(OFF)}}=5\Omega$, $T_J=65^{\circ}\text{C}$, $T_{\text{jmax}}=175^{\circ}\text{C}$, PF=0.8, Modulation rate=1



Note1: This graph is calculated value for reference based on the limitation of $T_{\text{jmax}}=175^{\circ}\text{C}$. The actual current out ability depends on inverter electrical, thermal and mechanic design. Please confirm it in actual application system.

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Module

Parameter	Conditions	Value	Unit
Isolation voltage	Main terminal to base plate, f =0Hz, t =1sec	4.0	kV
Material of module baseplate	-	Cu + Ni	-
Creepage distance	terminal to heatsink terminal to terminal	9	mm
Clearance	terminal to heatsink terminal to terminal	4.5	mm
Stray inductance module	$T_f = 65^{\circ}\text{C}$	8	nH
Module lead resistance, terminals – chip	$T_f = 65^{\circ}\text{C}$	0.2	m Ω
Mounting torque for module mounting	Screw M4 baseplate to heatsink	1.8 to 2.2	Nm
Weight	-	798	g

NTC Characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _c =25°C	-	5	-	k Ω
$\Delta R/R$	Deviation of R ₁₀₀	T _c =100°C, R ₁₀₀ =493 Ω	-5	-	5	%
P ₂₅	Power dissipation	T _c =25°C	-	-	20	mW
B _{25/50}	B-value	$R_2 = R_{25} \exp [B_{25/50} (1/T_2 - 1/(298,15 \text{ K}))]$	-	3375	-	K
B _{25/80}	B-value	$R_2 = R_{25} \exp [B_{25/80} (1/T_2 - 1/(298,15 \text{ K}))]$	-	3411	-	K
B _{25/100}	B-value	$R_2 = R_{25} \exp [B_{25/100} (1/T_2 - 1/(298,15 \text{ K}))]$	-	3433	-	K

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MOSFET Electrical Characteristics ($T_j=25^{\circ}\text{C}$ Unless Otherwise Specified, Chip)

Symbol	Parameter	Conditions		Value			Unit
				Min.	Typ.	Max.	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =600μA		1400	-	-	V
I _{DSS}	Zero gate voltage drain current	V _{DS} =1400V, V _{GS} =0V		-	60	-	μA
V _{GS(Th)}	Gate-source threshold voltage	I _D =120mA V _{DS} =V _{GS}	T _J =25°C	1.9	2.5	3.8	V
			T _J =175°C	-	1.60	-	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V, V _{DS} =0V, T _J =25°C		-	-	1200	nA
R _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =600A V _{GS} =20V	T _J =25°C	-	3.2	-	mΩ
			T _J =175°C	-	6.2	-	mΩ
	Static drain-source On-state resistance	I _D =600A V _{GS} =18V	T _J =25°C	-	3.5	-	mΩ
			T _J =175°C	-	6.5	-	mΩ
V _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =600A V _{GS} =20V	T _J =25°C	-	1.90	-	V
			T _J =175°C	-	3.7	-	V
		I _D =600A V _{GS} =18V	T _J =25°C	-	2.10	-	V
			T _J =175°C	-	3.9	-	V
C _{iss}	Input capacitance	V _{DS} =1000V V _{GS} =0V f=100kHz		-	28.62	-	nF
C _{oss}	Output capacitance			-	1.30	-	nF
C _{rss}	Reverse transfer capacitance			-	0.10	-	nF
Q _g	Total gate charge	V _{DS} =800V I _D =300A V _{GS} =+20/-5V		-	1620	-	nC
Q _{gs}	Gate to source charge			-	372	-	nC
Q _{gd}	Gate to drain charg			-	468	-	nC
R _{gint}	Internal gate resistance	f=1MHz		-	1.5	-	Ω
t _{d(on)}	Turn-on delay tim	V _{DD} =800V I _D =600A V _{GS} =+18/-4V R _{G(ON)} =3.3Ω R _{G(OFF)} =3.3Ω Inductive load Switching operation	T _J =25°C	-	71	-	ns
			T _J =150°C	-	63	-	
t _r	Rise time		T _J =25°C	-	59	-	ns
			T _J =150°C	-	48	-	
t _{d(off)}	Turn-off delay time		T _J =25°C	-	48	-	ns
			T _J =150°C	-	63	-	
t _f	Fall time		T _J =25°C	-	30	-	ns
			T _J =150°C	-	41	-	
E _{on}	Turn-on power dissipation		T _J =25°C	-	16.2	-	mJ
			T _J =150°C	-	22.9	-	
E _{off}	Turn-off power dissipation		T _J =25°C	-	4.4	-	mJ
			T _J =150°C	-	7.1	-	
R _{th(j-f)}	FET Thermal Resistance	Junction to cooling fluid ΔV/Δt=10dm³/min, T _f =65°C		-	0.084	-	K/W

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Body Diode Electrical Characteristics ($T_j=25^{\circ}\text{C}$ Unless Otherwise Specified, Chip)

Symbol	Parameter	Conditions		Value			Unit
				Min.	Typ.	Max.	
V _{SD}	Body Diode Forward Voltage	V _{GS} =-5V I _{SD} =600A	T _J =25°C	-	5.8	-	V
			T _J =175°C	-	5.2	-	
T _{rr}	Reverse Recovery Time	V _{RR} =800V I _D =600A MOSFET Side: V _{GS} =+18/-4V R _{G(ON)} =R _{G(OFF)} =3.3Ω Inductive loads Switching operation	T _J =25°C	-	44	-	ns
			T _J =150°C	-	51	-	
Q _{rr}	Reverse Recovery Charge		T _J =25°C	-	3.4	-	μC
			T _J =150°C	-	7.3	-	
E _{rr}	Diode Switching Power Dissipation		T _J =25°C	-	0.9	-	mJ
			T _J =150°C	-	2.8	-	

Test Conditions

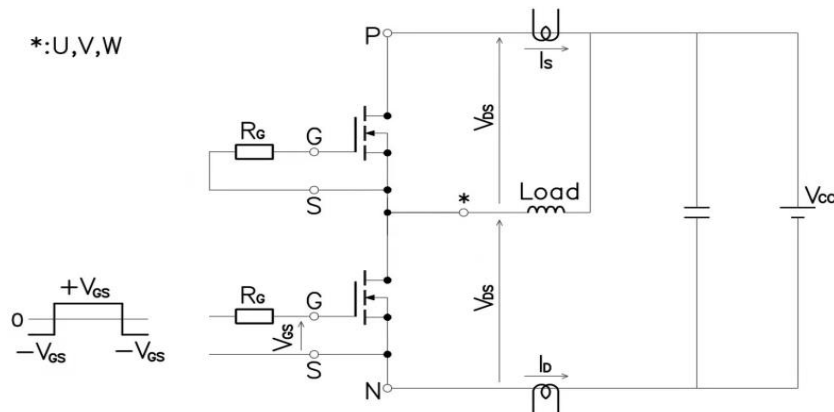


Figure 3. Switching Time Measure Circuit

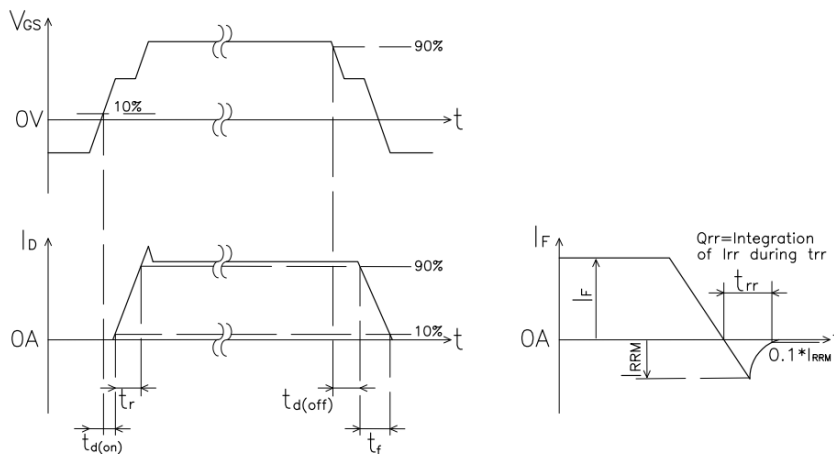


Figure 4. Switching Time Definition

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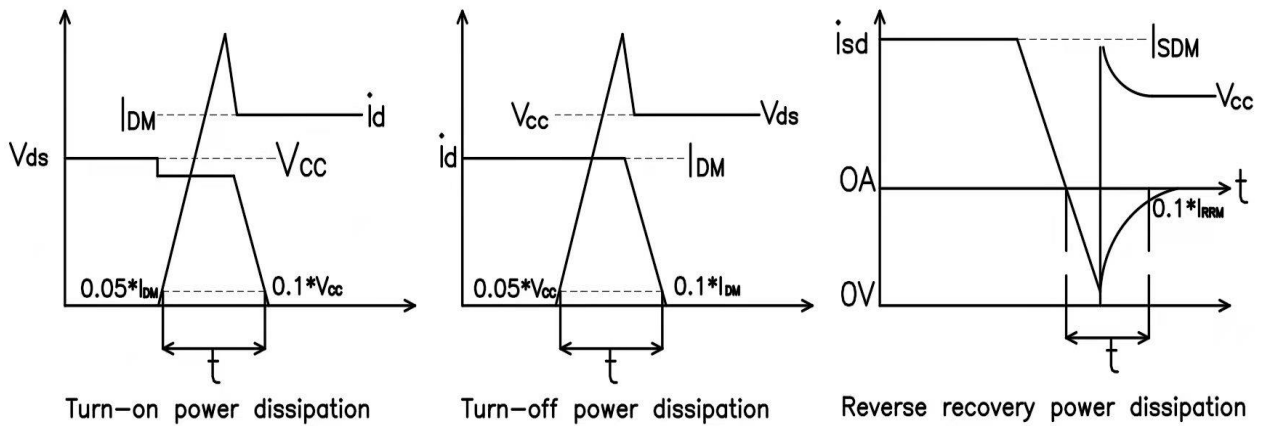


Figure 4. Switching Power Dissipation Definition

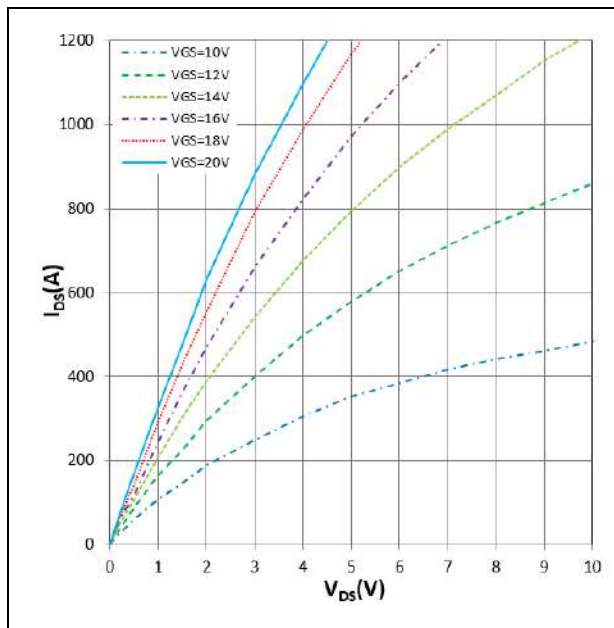


Figure 6. I_{DS} VS V_{DS}
 $T_J = 25^\circ\text{C}$, V_{GS} Parameter

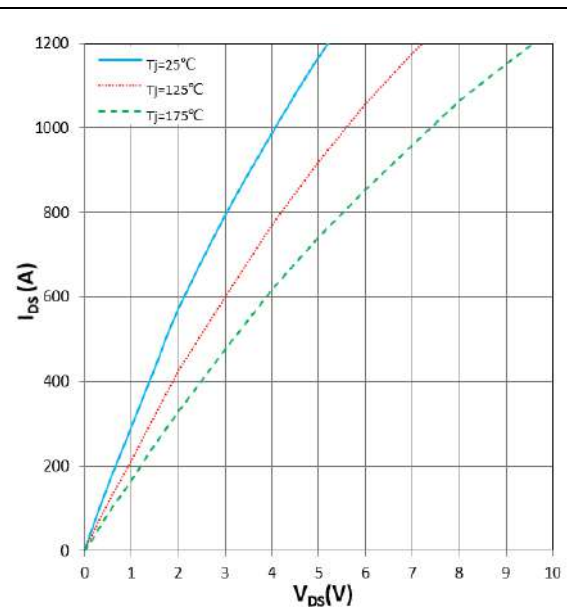


Figure 7. I_{DS} VS V_{DS}
 $V_{GS} = 18V$, T_J Parameter

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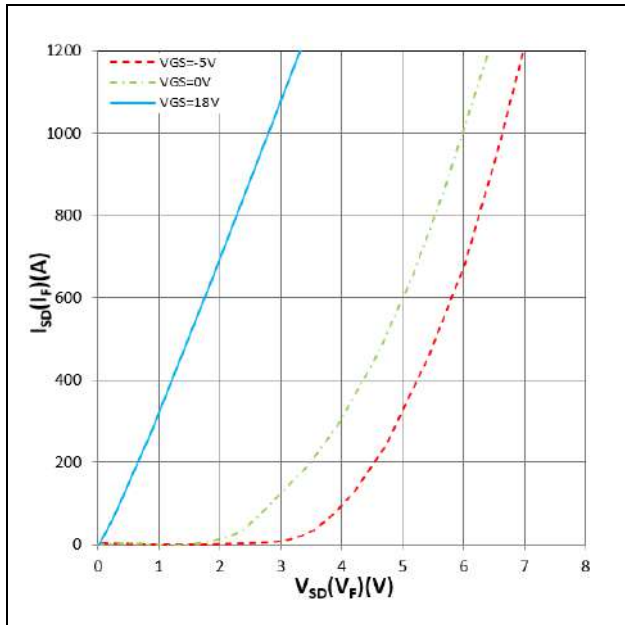


Figure 8. I_{DS} VS V_{DS}
 $T_J = 25^\circ\text{C}$, V_{GS} Parameter

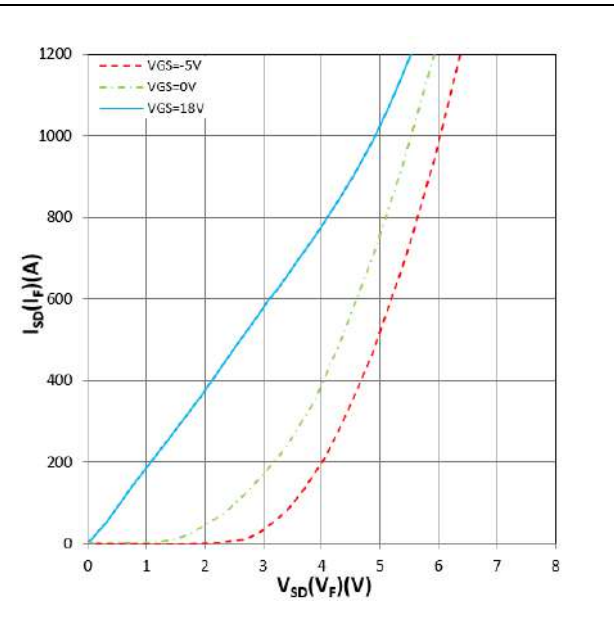


Figure 9. I_{DS} VS V_{DS}
 $T_J = 175^\circ\text{C}$, V_{GS} Parameter

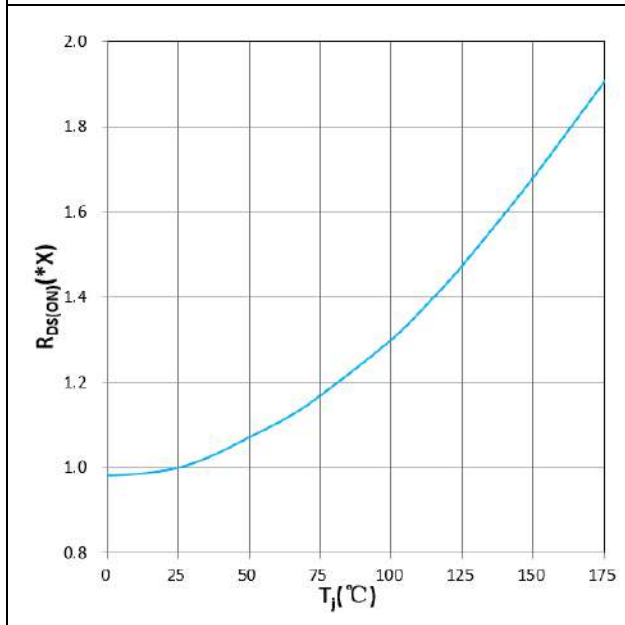


Figure 10. $R_{DS(ON)}$ VS T_J
 $V_{GS} = +20\text{V}$, $I_D = 600\text{A}$, $1.0X = 3.2\text{m}\Omega$

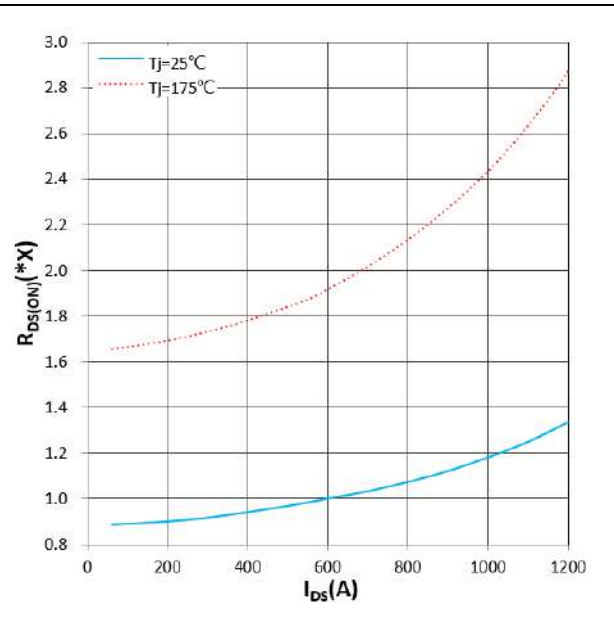


Figure 11. $R_{DS(ON)}$ VS I_{DS}
 $T_J = 25^\circ\text{C}$, $V_{GS} = +20\text{V}$, $1.0X = 3.2\text{m}\Omega$

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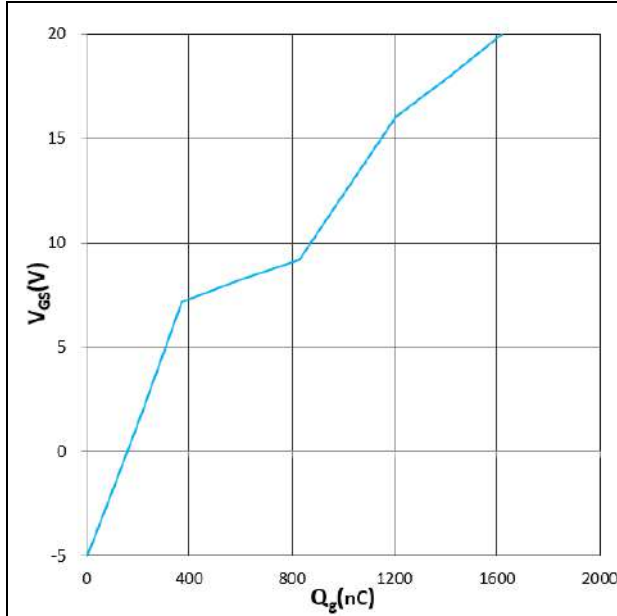


Figure 12. V_{GS} VS Q_g
 $T_j=25^{\circ}\text{C}$, $I_D=300\text{A}$, $V_{DS}=800\text{V}$

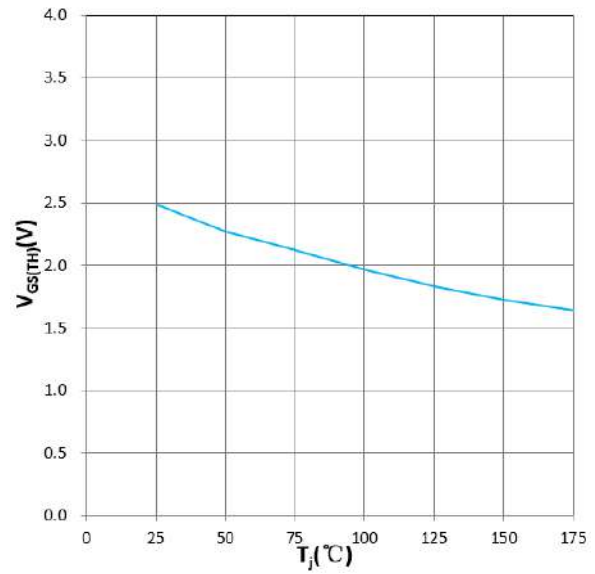


Figure 13. $V_{GS(Th)}$ VS T_j
 $V_{GS}=V_{DS}$, $I_D=120\text{mA}$

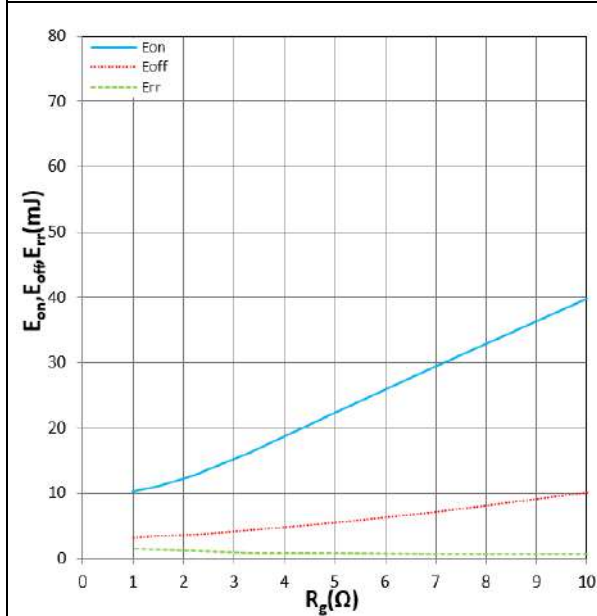


Figure 14. E_{on} , E_{off} , E_{rr} VS R_g
 $T_j=25^{\circ}\text{C}$, $V_{DD}=800\text{V}$, $I_D=600\text{A}$, $V_{GS}=+18\text{V}/-4\text{V}$
Inductive Load

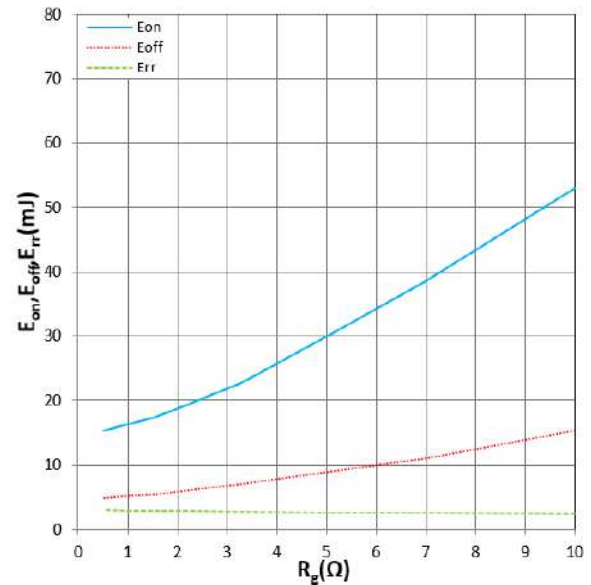


Figure 15. E_{on} , E_{off} , E_{rr} VS R_g
 $T_j=150^{\circ}\text{C}$, $V_{DD}=800\text{V}$, $I_D=600\text{A}$, $V_{GS}=+18\text{V}/-4\text{V}$
Inductive Load

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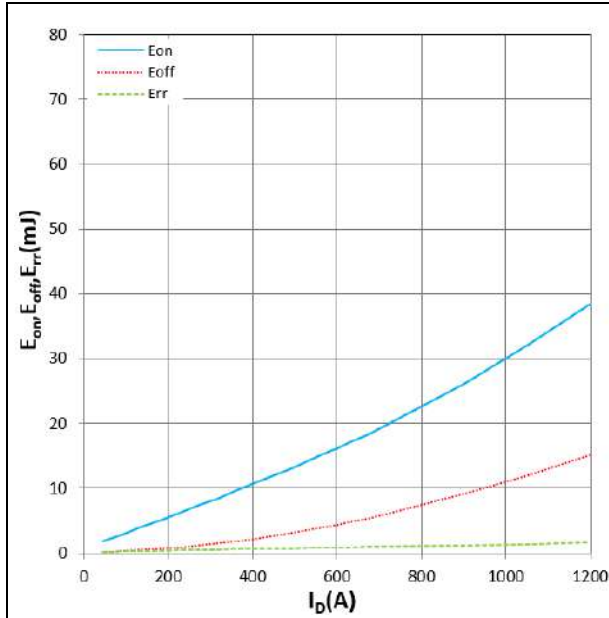


Figure 16. E_{on} , E_{off} , E_{rr} VS I_{DS}
 $T_j = 25^\circ\text{C}$, $V_{DD} = 800\text{V}$, $R_G = 3.3\Omega$, $V_{GS} = +18\text{V}/-4\text{V}$
 Inductive Load

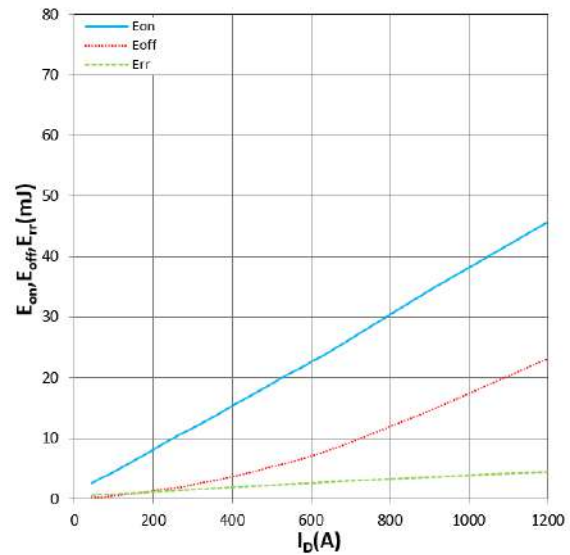


Figure 17. E_{on} , E_{off} , E_{rr} VS I_{DS}
 $T_j = 150^\circ\text{C}$, $V_{DD} = 800\text{V}$, $R_G = 3.3\Omega$, $V_{GS} = +18\text{V}/-4\text{V}$
 Inductive Load

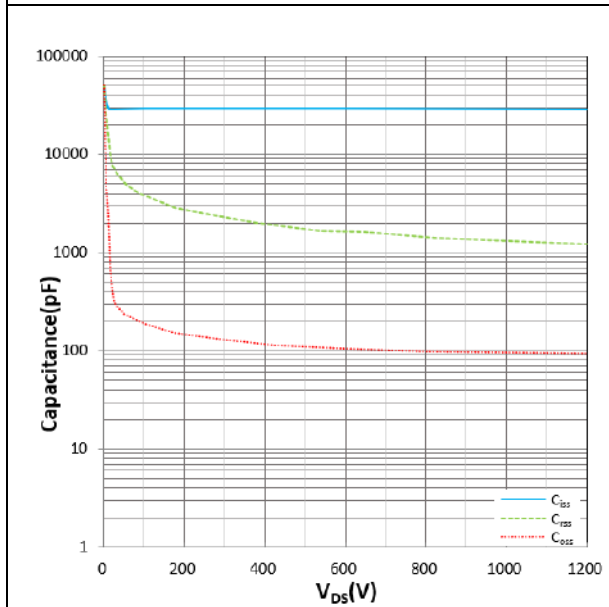


Figure 18. C_{iss} , C_{oss} , C_{rss} VS V_{DS}
 $V_{GS} = 0\text{V}$, $f = 100\text{kHz}$

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IMPORTANT NOTICE

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

Please contact the sales staff (sales@hiitio.com) for further information on the product, technology, delivery terms, conditions and prices.

Revision History

Document Version	Description of Changes
RevX.0.1	Released

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